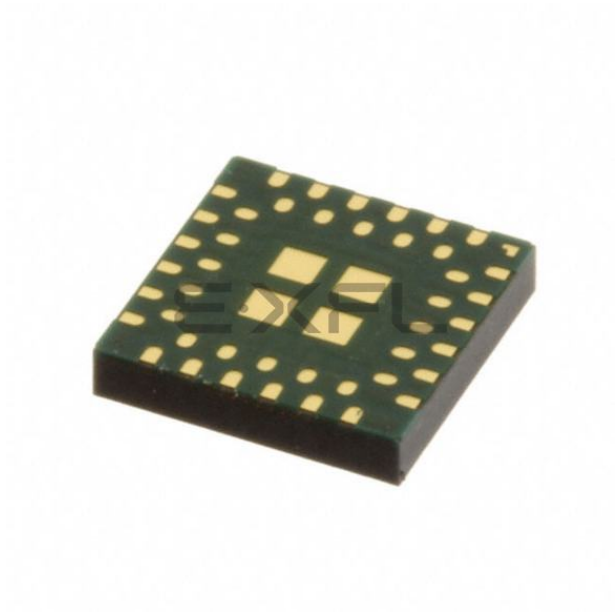

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	50MHz
Connectivity	I²C, SPI, UART/USART
Peripherals	DMA, WDT
Number of I/O	20
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 5x16b, 4x24b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	44-VFLGA Exposed Pad
Supplier Device Package	44-MAPLGA (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mkm14z64achh5

- Communication interfaces
  - One SPI module with FIFO support (supports 5V AMR operation)
  - One SPI module without FIFO (no AMR operation)
  - Two I2C modules with SMBus support
  - Two UART modules with ISO7816 support and Two UART without ISO 7816 support
  - Any one SCI can be used for IrDA operation. 5V AMR support on one SCI.

Symbol	Description	Min.	Max.	Unit
V_{DD}	1.0 V core supply voltage	0.9	1.1	V

3.2 Definition: Operating behavior

Unless otherwise specified, an *operating behavior* is a specified value or range of values for a technical characteristic that are guaranteed during operation if you meet the operating requirements and any other specified conditions.

3.2.1 Example

This is an example of an operating behavior:

Symbol	Description	Min.	Max.	Unit
I_{WP}	Digital I/O weak pullup/ pulldown current	10	130	µA

3.3 Definition: Attribute

An *attribute* is a specified value or range of values for a technical characteristic that are guaranteed, regardless of whether you meet the operating requirements.

3.3.1 Example

This is an example of an attribute:

Symbol	Description	Min.	Max.	Unit
CIN_D	Input capacitance: digital pins	—	7	pF

3.4 Definition: Rating

A *rating* is a minimum or maximum value of a technical characteristic that, if exceeded, may cause permanent chip failure:

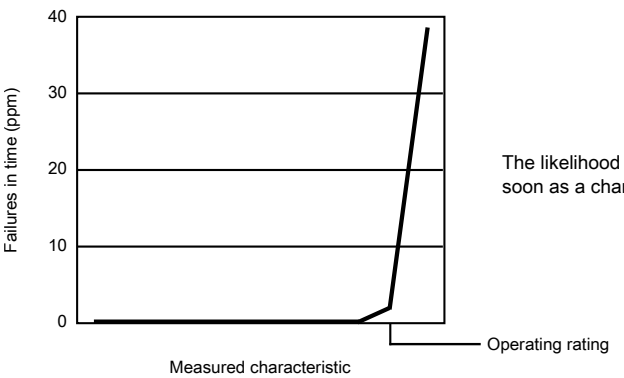
- *Operating ratings* apply during operation of the chip.
- *Handling ratings* apply when the chip is not powered.

3.4.1 Example

This is an example of an operating rating:

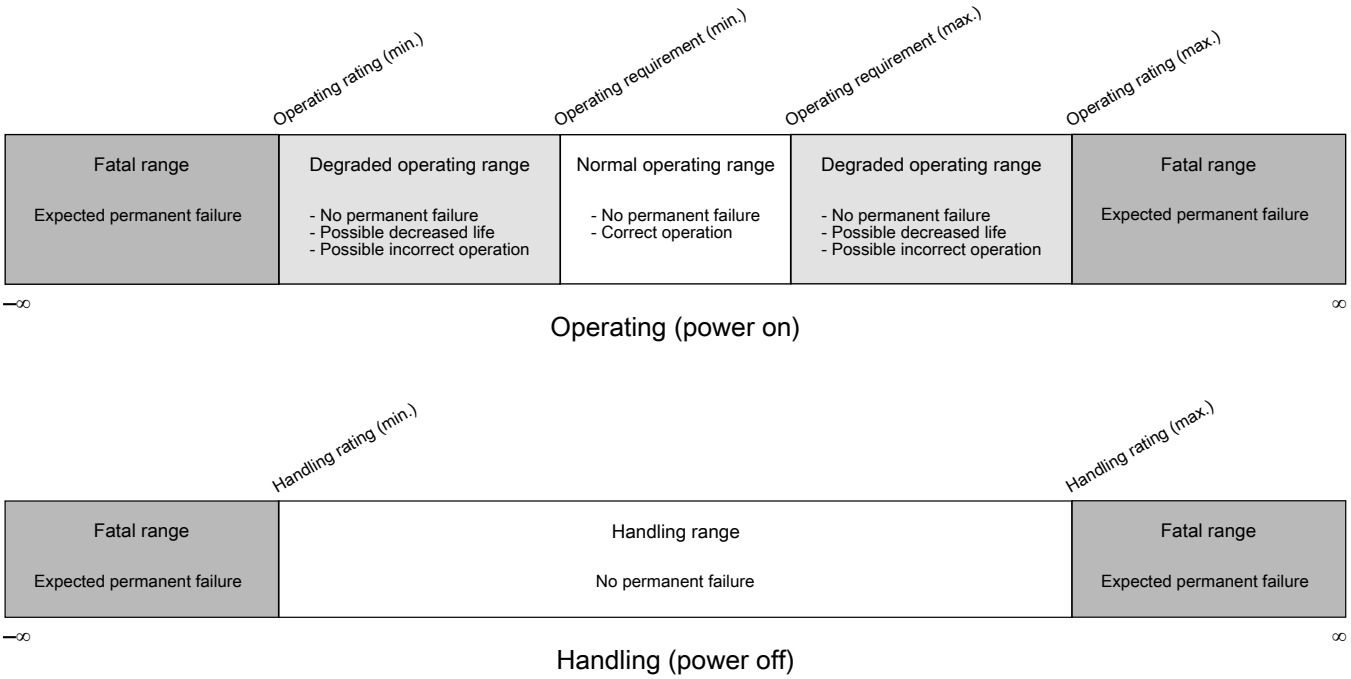
Symbol	Description	Min.	Max.	Unit
V_{DD}	1.0 V core supply voltage	–0.3	1.2	V

3.5 Result of exceeding a rating



The likelihood of permanent chip failure increases rapidly as soon as a characteristic begins to exceed one of its operating ratings.

3.6 Relationship between ratings and operating requirements



3.7 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.
- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.

3.8 Definition: Typical value

A *typical value* is a specified value for a technical characteristic that:

- Lies within the range of values specified by the operating behavior
- Given the typical manufacturing process, is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions

Typical values are provided as design guidelines and are neither tested nor guaranteed.

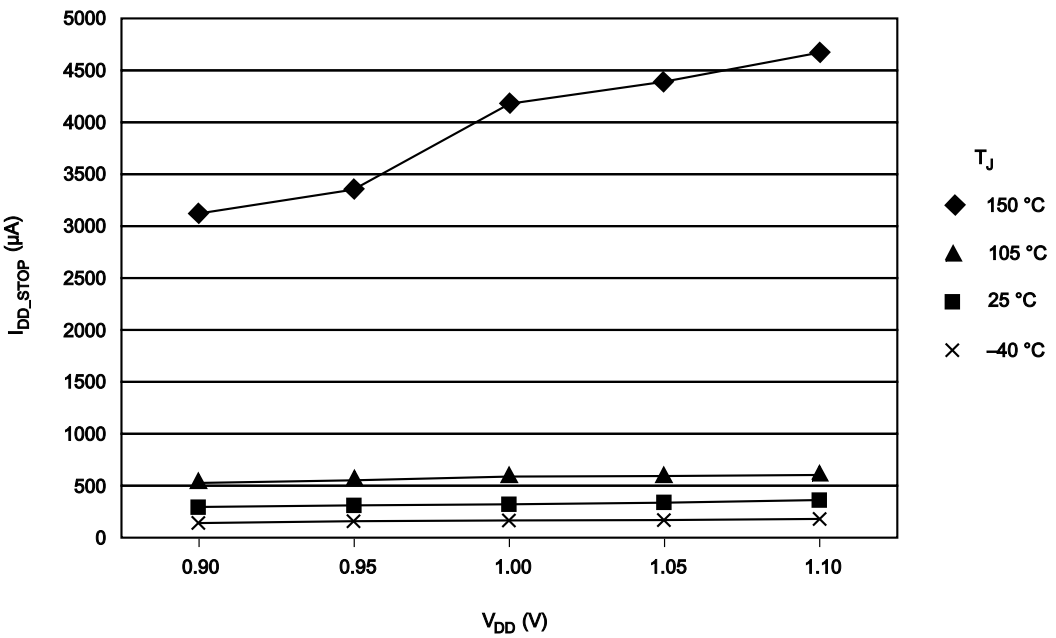
3.8.1 Example 1

This is an example of an operating behavior that includes a typical value:

Symbol	Description	Min.	Typ.	Max.	Unit
I_{WP}	Digital I/O weak pullup/pulldown current	10	70	130	µA

3.8.2 Example 2

This is an example of a chart that shows typical values for various voltage and temperature conditions:



3.9 Typical value conditions

Typical values assume you meet the following conditions (or other conditions as specified):

Symbol	Description	Value	Unit
T_A	Ambient temperature	25	°C
V_{DD}	3.3 V supply voltage	3.3	V

4.4 Voltage and current operating ratings

Symbol	Description	Min.	Max.	Unit
V_{DD}	Digital supply voltage	–0.3	3.6	V
V_{DIO}	Digital input voltage (except $\overline{RESET}$, EXTAL, and XTAL)	–0.3	V_{DD} + 0.3	V
$V_{DTamper}$	Tamper input voltage	–0.3	V_{BAT} + 0.3	V
V_{AIO}	Analog[1], $\overline{RESET}$, EXTAL, and XTAL input voltage	–0.3	V_{DD} + 0.3	V
I_D	Instantaneous maximum current single pin limit (applies to all port pins)	–25	25	mA
V_{DDA}	Analog supply voltage	V_{DD} – 0.3	V_{DD} + 0.3	V
V_{BAT}	RTC battery supply voltage	–0.3	3.6	V

1. Analog pins are defined as pins that do not have an associated general purpose I/O port function.

5 General

5.1 AC electrical characteristics

Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured at the 20% and 80% points, as shown in the following figure.

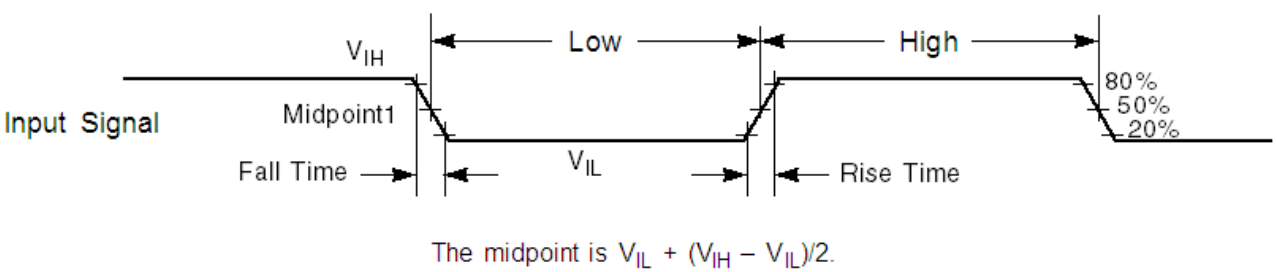


Figure 1. Input signal measurement reference

5.2 Nonswitching electrical specifications

Table 6. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes

I_{DD_VBAT}	Average current when VDD is OFF and LFSR and Tamper clocks set to 2 Hz.
	• @ 3.0 V
	  • 25 °C
	  • -40 °C
	  • 105 °C
		—	1.3 [7]	3
				2.5
				16
					µA
					µA
					µA
						8, 9

1. See AFE specification for IDDA.
2. 50 MHz core and system clock, 25 MHz bus clock, and 25 MHz flash clock. MCG configured for FBE mode. All peripheral clocks disabled.
3. Should be reduced by 500 µA.
4. 2 MHz core, system, bus clock, and 1 MHz flash clock. MCG configured for BLPE mode. All peripheral clocks disabled. Code executing while (1) loop from flash.
5. 2 MHz core, system and bus clock, and 1MHz flash clock. MCG configured for BLPE mode. All peripheral clocks enabled but peripherals are not in active operation. Code executing while (1) loop from flash.
6. 2 MHz core, system and bus clock, and 1 MHz flash clock. MCG configured for BLPE mode. All peripheral clocks disabled. No flash accesses; some activity on DMA & RAM assumed.
7. Current consumption will vary with number of CPU accesses done and is dependent on the frequency of the accesses and frequency of bus clock. Number of CPU accesses should be optimized to get optimal current value.
8. Includes 32 kHz oscillator current and RTC operation.
9. An external power switch for VBAT should be present on board to have better battery life and keep VBAT pin powered in all conditions. There is no internal power switch in RTC.

5.2.6 EMC radiated emissions operating behaviors

Table 7. EMC radiated emissions operating behaviors

Symbol	Description	Frequency band (MHz)	Typ.	Unit	Notes
V_{RE1}	Radiated emissions voltage, band 1	0.15–50	14	dBµV	1, 2
V_{RE2}	Radiated emissions voltage, band 2	50–150	16	dBµV	
V_{RE3}	Radiated emissions voltage, band 3	150–500	12	dBµV	
V_{RE4}	Radiated emissions voltage, band 4	500–1000	5	dBµV	
V_{RE_IEC}	IEC level	0.15–1000	M	—	2, 3

1. Determined according to IEC Standard 61967-1, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 1: General Conditions and Definitions* and IEC Standard 61967-2, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 2: Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*. Measurements were made while the microcontroller was running basic application code. The reported emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.
2. V_{DD} = 3.3 V, T_A = 25 °C, f_{OSC} = 10 MHz (crystal), f_{SYS} = 50 MHz, f_{BUS} = 25 MHz
3. Specified according to Annex D of IEC Standard 61967-2, *Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*

5.3.2 General switching specifications

These general purpose specifications apply to all signals configured for GPIO, UART, and I^2C signals.

Table 10. General switching specifications

Symbol	Description	Min.	Max.	Unit	Notes
	GPIO pin interrupt pulse width (digital glitch filter disabled) — Synchronous path	1.5	—	Bus clock cycles	1
	GPIO pin interrupt pulse width (digital glitch filter disabled) — Asynchronous path	16	—	ns	2
	External reset pulse width (digital glitch filter disabled)	100	—	ns	2
	Port rise and fall time—Low (All pins) and high drive (only PTC2) strength				3
	• Slew disabled				
	• $1.71 \le V_{DD} \le 2.7$ V	—	8	ns	
	• $2.7 \le V_{DD} \le 3.6$ V	—	5	ns	
	• Slew enabled				
	• $1.71 \le V_{DD} \le 2.7$ V	—	27	ns	
	• $2.7 \le V_{DD} \le 3.6$ V	—	16	ns	

1. The greater synchronous and asynchronous timing must be met.
2. This is the shortest pulse that is guaranteed to be recognized.
3. Only PTC2 has high drive capability and load is 75 pF, other pins load (low drive) is 25 pF.

5.4 Thermal specifications

5.4.1 Thermal operating requirements

Table 11. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
T_J	Die junction temperature	–40	105	°C	
T_A	Ambient temperature	–40	85	°C	1

1. Maximum T_A can be exceeded only if the user ensures that T_J does not exceed the maximum. The simplest method to determine T_J is: $T_J = T_A + \theta_{JA} \times$ chip power dissipation

6.1 Core modules

6.1.1 Single Wire Debug (SWD)

Table 12. SWD switching characteristics at 2.7 V (2.7-3.6 V)

Symbol	Description	Value	Unit	Notes
SWD CLK	Frequency of SWD operation	20	MHz	1
Inputs, tSUI	Data setup time	5	ns	1
inputs,tHI	Data hold time	0	ns	1
after clock edge, tDVO	Data valid Time	32	ns	1
tHO	Data Valid Hold	0	ns	1

1. Input transition assumed =1 ns. Output transition assumed = 50 pf.

Table 13. Switching characteristics at 1.7 V (1.7-3.6 V)

Symbol	Description	Value	Unit	Notes
SWD CLK	Frequency of SWD operation	18	MHz	
Inputs, tSUI	Data setup time	4.7	ns	
inputs,tHI	Data hold time	0	ns	
after clock edge, tDVO	Data valid Time	49.4	ns	2
tHO	Data Valid Hold	0	ns	

1. Frequency of SWD clock (18 Mhz) is applicable only in case the input setup time of the device outside is not more than 6.15 ns, else the frequency of SWD clock would need to be lowered.

6.1.2 Analog Front End (AFE)

AFE switching characteristics at (2.7 V-3.6 V)

Case1: Clock is coming In and Data is also coming In (XBAR ports timed with respect to the XBAR ports timed with respect to AFE clock defined at pad ptb[7] and pte[3])

Table 14. AFE switching characteristics (2.7 V-3.6 V)

Symbol	Description	Value	Unit	Notes
AFE CLK	Frequency of operation	10	MHz	1
Inputs, tSUI	Data setup time	5	ns	1
inputs,tHI	Data hold time	0	ns	1

1. Input Transition: 1ns. Output Load: 50 pf.

Case 2: Clock is going Out and Data is coming In (XBAR ports timed with respect to generated clock defined at the XBAR out ports)

Table 15. AFE switching characteristics (2.7V-3.6V)

Symbol	Description	Value	Unit	Notes
AFE CLK	Frequency of operation	6.2	MHz	
Inputs, tSUI	Data setup time	36	ns	
inputs,tHI	Data hold time	0	ns	

AFE switching characteristics at (1.7 V-3.6 V)

Case1: Clock is coming In and Data is also coming In (XBAR ports timed with respect to AFE clock defined at pad ptb[7] and pte[3])

Table 16. AFE switching characteristics (1.7 V-3.6 V)

Symbol	Description	Value	Unit	Notes
AFE CLK	Frequency of operation	10	MHz	
Inputs, tSUI	Data setup time	5.1	ns	
inputs,tHI	Data hold time	0	ns	

Case 2: Clock is going Out and Data is coming In (XBAR ports timed with respect to generated clock defined at XBAR out ports)

Table 17. AFE switching characteristics (1.7 V-3.6 V)

Symbol	Description	Value	Unit	Notes
AFE CLK	Frequency of operation	6.2	MHz	
Inputs, tSUI	Data setup time	54	ns	
inputs,tHI	Data hold time	0	ns	

6.2 Clock modules

6.2.1 MCG specifications

Table 18. MCG specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{ints_ft}	Internal reference frequency (slow clock) — factory trimmed at nominal VDD and 25 °C	—	32.768	—	kHz	

Table continues on the next page...

Table 18. MCG specifications (continued)

Symbol	Description		Min.	Typ.	Max.	Unit	Notes
Δf_{ints_t}	Total deviation of internal reference frequency (slow clock) over voltage and temperature		—	+0.5/-0.7	—	%	
Δf_{ints_t}	Total deviation of internal reference frequency (slow clock) over fixed voltage and full operating temperature range		-2	—	+2	%	
f_{ints_t}	Internal reference frequency (slow clock) — user trimmed		31.25	—	39.0625	kHz	
$\Delta_{fdco\_res\_t}$	Resolution of trimmed average DCO output frequency at fixed voltage and temperature — using SCTRIM and SCFTRIM		—	± 0.3	± 0.6	$\%f_{dco}$	1
Δf_{dco_t}	Total deviation of trimmed average DCO output frequency over voltage and temperature		—	+0.5/-0.7		$\%f_{dco}$	1
Δf_{dco_t}	Total deviation of trimmed average DCO output frequency over fixed voltage and temperature range of 0–70°C		—	± 0.4	—	$\%f_{dco}$	1
f_{intf_ft}	Internal reference frequency (fast clock) — factory trimmed at nominal VDD and 25°C		—	4	—	MHz	
Δf_{intf_t}	Total deviation of internal reference frequency (fast clock) over voltage and temperature — factory trimmed at nominal VDD and 25°C		—	+1/-2	—	%	
f_{intf_t}	Internal reference frequency (fast clock) — user trimmed at nominal VDD and 25 °C		3	—	5	MHz	
f_{loc_low}	Loss of external clock minimum frequency — RANGE = 00		(3/5) x f_{ints_t}	—	—	kHz	
f_{loc_high}	Loss of external clock minimum frequency — RANGE = 01, 10, or 11		(16/5) x f_{ints_t}	—	—	kHz	
FLL							
f_{dco}	DCO output frequency range	Low-range (DRS=00) 640 × f_{ints_t}	20	20.97	22	MHz	2, 3
		Mid-range (DRS=01) 1280 × f_{ints_t}	40	41.94	45	MHz	
		Mid-high range (DRS=10) 1920 × f_{ints_t}	60	62.91	67	MHz	
		High-range (DRS=11) 2560 × f_{ints_t}	80	83.89	90	MHz	

Table continues on the next page...

Table 24. Flash command timing specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{pgmchk}	Program Check execution time	—	—	45	µs	1
t_{rdrsrc}	Read Resource execution time	—	—	30	µs	1
t_{pgm4}	Program Longword execution time	—	65	145	µs	—
t_{ersscr}	Erase Flash Sector execution time	—	14	114	ms	2
t_{rd1all}	Read 1s All Blocks execution time	—	—	1.8	ms	—
t_{rdonce}	Read Once execution time	—	—	25	µs	1
$t_{pgmonce}$	Program Once execution time	—	65	—	µs	—
t_{ersall}	Erase All Blocks execution time	—	88	650	ms	2
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	30	µs	1

1. Assumes 25 MHz flash clock frequency.
2. Maximum times for erase parameters based on expectations at cycling end-of-life.

6.3.1.3 Flash high voltage current behaviors

Table 25. Flash high voltage current behaviors

Symbol	Description	Min.	Typ.	Max.	Unit
I_{DD_PGM}	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
I_{DD_ERS}	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

6.3.1.4 Reliability specifications

Table 26. NVM reliability specifications

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
Program Flash						
$t_{nvmretp10k}$	Data retention after up to 10 K cycles	5	50	—	years	—
$t_{nvmretp1k}$	Data retention after up to 1 K cycles	20	100	—	years	—
$n_{nvmcycp}$	Cycling endurance	10 K	50 K	—	cycles	2

1. Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25 °C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.
2. Cycling endurance represents number of program/erase cycles at –40 °C ≤ T_j ≤ 125 °C.

6.4 Analog

6.4.1 ADC electrical specifications

All ADC channels meet the 12-bit single-ended accuracy specifications.

6.4.1.1 16-bit ADC operating conditions

Table 27. 16-bit ADC operating conditions

Symbol	Description	Conditions	Min.	Typ.[1]	Max.	Unit	Notes
V_{DDA}	Supply voltage	Absolute	1.71	—	3.6	V	—
ΔV_{DDA}	Supply voltage	Delta to V_{DD} ($V_{DD} - V_{DDA}$)	-100	0	+100	mV	2
ΔV_{SSA}	Ground voltage	Delta to V_{SS} ($V_{SS} - V_{SSA}$)	-100	0	+100	mV	2
V_{REFH}	ADC reference voltage high		1.13	V_{DDA}	V_{DDA}	V	
V_{REFL}	ADC reference voltage low		V_{SSA}	V_{SSA}	V_{SSA}	V	
V_{ADIN}	Input voltage		V_{REFL}	—	V_{REFH}	V	—
C_{ADIN}	Input capacitance	• 16-bit mode • 8-bit / 10-bit / 12-bit modes	— —	8 4	10 5	pF	—
R_{ADIN}	Input series resistance		—	2	5	kΩ	—
R_{AS}	Analog source resistance (external)	12-bit modes f_{ADCK} < 4 MHz	—	—	5	kΩ	3
f_{ADCK}	ADC conversion clock frequency	≤ 12-bit mode	1.0	—	18.0	MHz	4
f_{ADCK}	ADC conversion clock frequency	16-bit mode	2.0	—	12.0	MHz	4
C_{rate}	ADC conversion rate	≤ 12-bit modes No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	20.000	—	818.330	Ksps	5
C_{rate}	ADC conversion rate	16-bit mode No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	37.037	—	461.467	Ksps	5

1. Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 1.0 MHz, unless otherwise stated. Typical values are for reference only, and are not tested in production.
2. DC potential difference.
3. This resistance is external to MCU. To achieve the best results, the analog source resistance must be kept as low as possible. The results in this data sheet were derived from a system that had < 8 Ω analog source resistance. The R_{AS}/C_{AS} time constant should be kept to < 1 ns.
4. To use the maximum ADC conversion clock frequency, CFG2[ADHSC] must be set and CFG1[ADLPC] must be clear.
5. For guidelines and examples of conversion rate calculation, download the ADC calculator tool.

Table 28. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Symbol	Description	Conditions[1]	Min.	Typ.[2]	Max.	Unit	Notes
E_{FS}	Full-scale error	• 12-bit modes • <12-bit modes	— —	–4 –1.4	–5.4 –1.8	LSB[4]	$V_{ADIN} = V_{DDA}$[5]
E_Q	Quantization error	• 16-bit modes • 12-bit modes	— —	–1 to 0 —	— ±0.5	LSB[4]	
ENOB	Effective number of bits	16-bit single-ended mode • Avg = 32 • Avg = 4	12.8 11.9 12.2 11.4	14.5 13.8 13.9 13.1	— — — —	bits bits bits bits	6
SINAD	Signal-to-noise plus distortion	See ENOB	6.02 × ENOB + 1.76			dB	
THD	Total harmonic distortion	16-bit single-ended mode • Avg = 32	— —	-94 -85	— —	dB dB	7
SFDR	Spurious free dynamic range	16-bit single-ended mode • Avg = 32	82 78	95 90	— —	dB dB	7
E_{IL}	Input leakage error		$I_{In} \times R_{AS}$			mV	I_{In} = leakage current (refer to the MCU's voltage and current operating ratings)
	Temp sensor slope	Across the full temperature range of the device	1.55	1.62	1.69	mV/°C	8
V_{TEMP25}	Temp sensor voltage	25 °C	706	716	726	mV	8

1. All accuracy numbers assume the ADC is calibrated with $V_{REFH} = V_{DDA}$
2. Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 2.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
3. The ADC supply current depends on the ADC conversion clock speed, conversion rate and ADC_CFG1[ADLPC] (low power). For lowest power operation, ADC_CFG1[ADLPC] must be set, the ADC_CFG2[ADHSC] bit must be clear with 1 MHz ADC conversion clock speed.
4. 1 LSB = $(V_{REFH} - V_{REFL})/2^N$
5. ADC conversion clock < 16 MHz, Max hardware averaging (AVGE = %1, AVGS = %11)
6. Input data is 100 Hz sine wave. ADC conversion clock < 12 MHz.
7. Input data is 1 kHz sine wave. ADC conversion clock < 12 MHz.
8. ADC conversion clock < 3 MHz

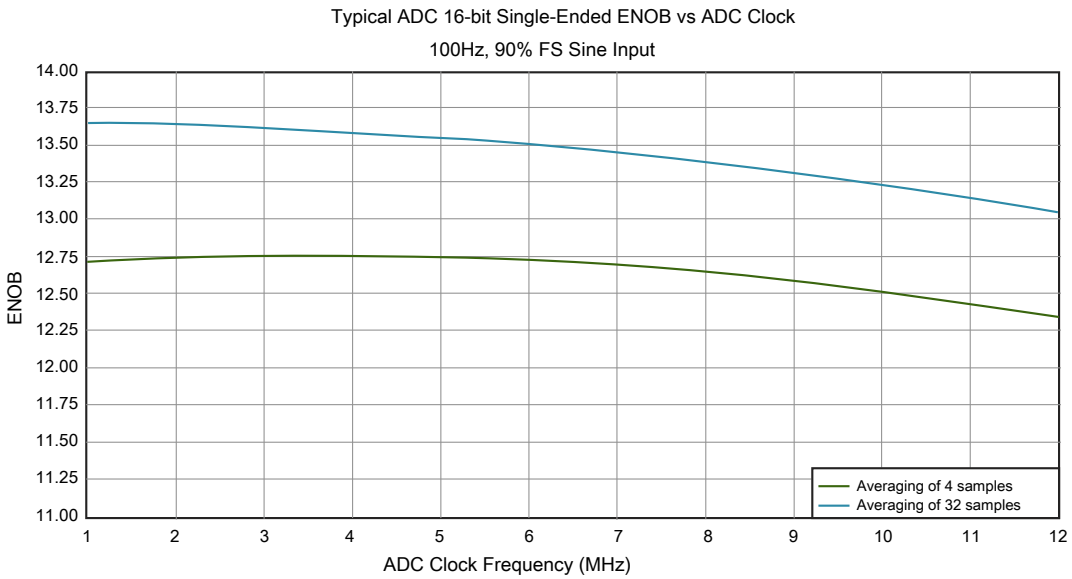


Figure 3. Typical ENOB vs. ADC_CLK for 16-bit single-ended mode

6.4.2 CMP and 6-bit DAC electrical specifications

Table 29. Comparator and 6-bit DAC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V_{DD}	Supply voltage	1.71	—	3.6	V
I_{DDHS}	Supply current, High-speed mode (EN=1, PMODE=1)	—	—	200	µA
I_{DDLS}	Supply current, low-speed mode (EN=1, PMODE=0)	—	—	20	µA
V_{AIN}	Analog input voltage	V_{SS} – 0.3	—	V_{DD}	V
V_{AIO}	Analog input offset voltage	—	—	20	mV
V_H	Analog comparator hysteresis[1] • CR0[HYSTCTR] = 00 • CR0[HYSTCTR] = 01 • CR0[HYSTCTR] = 10 • CR0[HYSTCTR] = 11	— — — —	5 10 20 30	— — — —	mV mV mV mV
V_{CMPOh}	Output high	V_{DD} – 0.5	—	—	V
V_{CMPOl}	Output low	—	—	0.5	V
t_{DHS}	Propagation delay, high-speed mode (EN=1, PMODE=1)	20	50	200	ns
t_{DLS}	Propagation delay, low-speed mode (EN=1, PMODE=0)	80	250	600	ns
	Analog comparator initialization delay[2]	—	—	40	µs
I_{DAC6b}	6-bit DAC current adder (enabled)	—	7	—	µA
INL	6-bit DAC integral non-linearity	–0.5	—	0.5	LSB[3]
DNL	6-bit DAC differential non-linearity	–0.3	—	0.3	LSB

Table 34. ΣΔ ADC + PGA specifications (continued)

Symbol	Description	Conditions	Min	Typ[1]	Max	Unit	Notes
E_{offset}	Offset Error	Gain=01, V_{pp}=1000 mV (full range diff.)			+/- 5	mV	
$\Delta Offset_{Temp}$	Offset Temperature Drift[3]	Gain=01, V_{pp}=1000mV (full range diff.)			+/- 25	ppm/°C	
$\Delta Gain_{Temp}$	Gain Temperate Drift - Gain error caused by temperature drifts[4]	• Gain=01, V_{pp}=500mV (differential ended) • Gain=32, V_{pp}=15mV (differential ended)			+/- 75	ppm/°C	
$PSRR_{AC}$	AC Power Supply Rejection Ratio	Gain=01, VCC = 3V ± 100mV, f_{IN} = 50 Hz		60		dB	
XT	Crosstalk (with the input of the affected channel grounded)	Gain=01, V_{id} = 500 mV, f_{IN} = 50 Hz			-100	dB	
f_{MCLK}	Modulator Clock Frequency Range	Normal Mode Low-Power Mode	0.03 0.03		6.5 1.6	MHz	
I_{DDA_PGA}	Current consumption by PGA (each channel)	Normal Mode (f_{MCLK} = 6.144 MHz, OSR= 2048) Low-Power Mode (f_{MCLK} = 0.768MHz, OSR= 256)			2.6 0	mA	5
I_{DDA_ADC}	Current Consumption by ADC (each chanel)	Normal Mode (f_{MCLK} = 6.144 MHz, OSR= 2048) Low-Power Mode (f_{MCLK} = 0.768MHz, OSR= 256)			1.4 0.5	mA	
R_{as}	Equivalent input impedance per single channel	PGA enabled		8		kΩ	

1. Typical values assume VDDA = 3.0 V, Temp = 25°C, f_{MCLK} = 6.144 MHz, OSR = 2048 for Normal mode and f_{MCLK} = 768 kHz, OSR = 256 for Low-Power Mode unless otherwise stated. Typical values are for reference only and are not tested in production.
2. The full-scale input range in single-ended mode is 0.5Vpp
3. Represents combined offset temperature drift of the PGA, SD ADC and Internal 1.2 VREF blocks; Defined by shorting both differential inputs to ground.
4. Represents combined gain temperature drift of the PGA, SD ADC and Internal 1.2 VREF blocks.
5. PGA is disabled in low-power modes.

6.4.4.2 ΣΔ ADC Standalone specifications

Table 35. ΣΔ ADC standalone specifications

Symbol	Description	Conditions	Min	Typ[1]	Max	Unit	Notes
f_{Nyq}	Input bandwidth	Normal Mode Low-Power Mode	1.5 1.5	1.5 1.5	1.5 1.5	kHz	
V_{CM}	Input Common Mode Reference		0		0.8	V	

Table continues on the next page...

1. Typical values assume VDDA = 3.0 V, Temp = 25°C, f_{MCLK} = 6.144 MHz, OSR = 2048 for Normal mode and f_{MCLK} = 768 kHz, OSR = 256 for Low-Power Mode unless otherwise stated. Typical values are for reference only and are not tested in production.
2. Represent combined gain temperature drift of the SD ADC, and Internal 1.2 VREF blocks.
3. Represent combined offset temperature drift of the SD ADC, and Internal 1.2 VREF blocks; Defined by shorting both differential inputs to ground.

6.4.4.3 External modulator interface

The external modulator interface on this device comprises of a Clock signal and 1-bit data signal. Depending on the modulator device being used the interface works as follows:

- Clock supplied to external modulator which drives data on rising edge and the KM device captures it on falling edge or next rising edge.
- Clock and data are supplied by external modulator and KM device can sample it on falling edge or next rising edge.

Depending on control bit in AFE, the sampling edge is changed.

6.5 Timers

See General switching specifications.

6.6 Communication interfaces

6.6.1 I2C switching specifications

See General switching specifications.

6.6.2 UART switching specifications

See General switching specifications.

6.6.3 SPI switching specifications

The Serial Peripheral Interface (SPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The following table provides some reference values to be met on SoC.

Table 36. SPI switching characteristics at 2.7 V (2.7 - 3.6)

Description	Min.	Max.	Unit	Notes
Frequency of operation (F_{sys})	—	50	MHz	1
SCK frequency • Master • Slave	2	12.5 12.5	MHz Mhz	3
SCK Duty Cycle	50%	—	—	
Data Setup Time (inputs, tSUI) • Master • Slave	25 3		ns	
Input Data Hold Time (inputs, tHI) • Master • Slave	0 1		ns	
Data hold time (outputs, tHO) • Master • Slave	0 0		ns	
Data Valid Out Time (after SCK edge, tDVO) • Master • Slave	13 28		ns	
Rise time input • Master • Slave	1 1		ns	
Fall time input • Master • Slave	1 1		ns	
Rise time output • Master • Slave	8.9 8.9		ns	
Fall time output • Master • Slave	7.8 7.8		ns	

1. SPI modules will work on core clock.
2. F_{sys}/(Max Divider Value from registers)
3. F_{SYS}/2 in Master mode and F_{SYS}/4 in Slave mode. F_{SYS}/4 in Master as well as Slave Modes, where F_{SYS}=50Mhz

NOTE

The values assumed for input transition and output load are:
Input transition = 1 ns Output load = 50 pF

Table 37. SPI switching characteristics at 1.7 V (1.7 - 3.6)

Description	Min.	Max.	Unit	Notes
Frequency of operation (F_{sys})	—	50	MHz	

Table continues on the next page...

Table 38. SPI switching characteristics at 1.7 V (1.7 - 3.6) (continued)

Description	Min.	Max.	Unit	Notes
Rise time input • Master • Slave	 1 1		ns	
Fall time input • Master • Slave	 1 1		ns	
Rise time output • Master • Slave	 30.4 30.4		ns	
Fall time output • Master • Slave	 33.5 29.0		ns	

Table 39. SPI switching characteristics at 2.7 V (2.7 - 3.6)

Description	Min.	Max.	Unit	Notes
Data Setup Time (inputs, tSUI) • Master • Slave	 29 4		ns	
Input Data Hold Time (inputs, tHI) • Master • Slave	 0 1		ns	
Data hold time (outputs, tHO) • Master • Slave	 0 0		ns	
Data Valid Out Time (after SCK edge, tDVO) • Master • Slave	 49 49		ns	
Rise time input • Master • Slave	 1 1		ns	
Fall time input • Master • Slave	 1 1		ns	
Rise time output • Master • Slave	 17.3 17.3		ns	
Fall time output • Master • Slave	 16.6 16.0		ns	

6.7 Human-Machine Interfaces (HMI)

8.3.3 44-pin LGA

Figure below shows the 44-pin LGA pinouts.

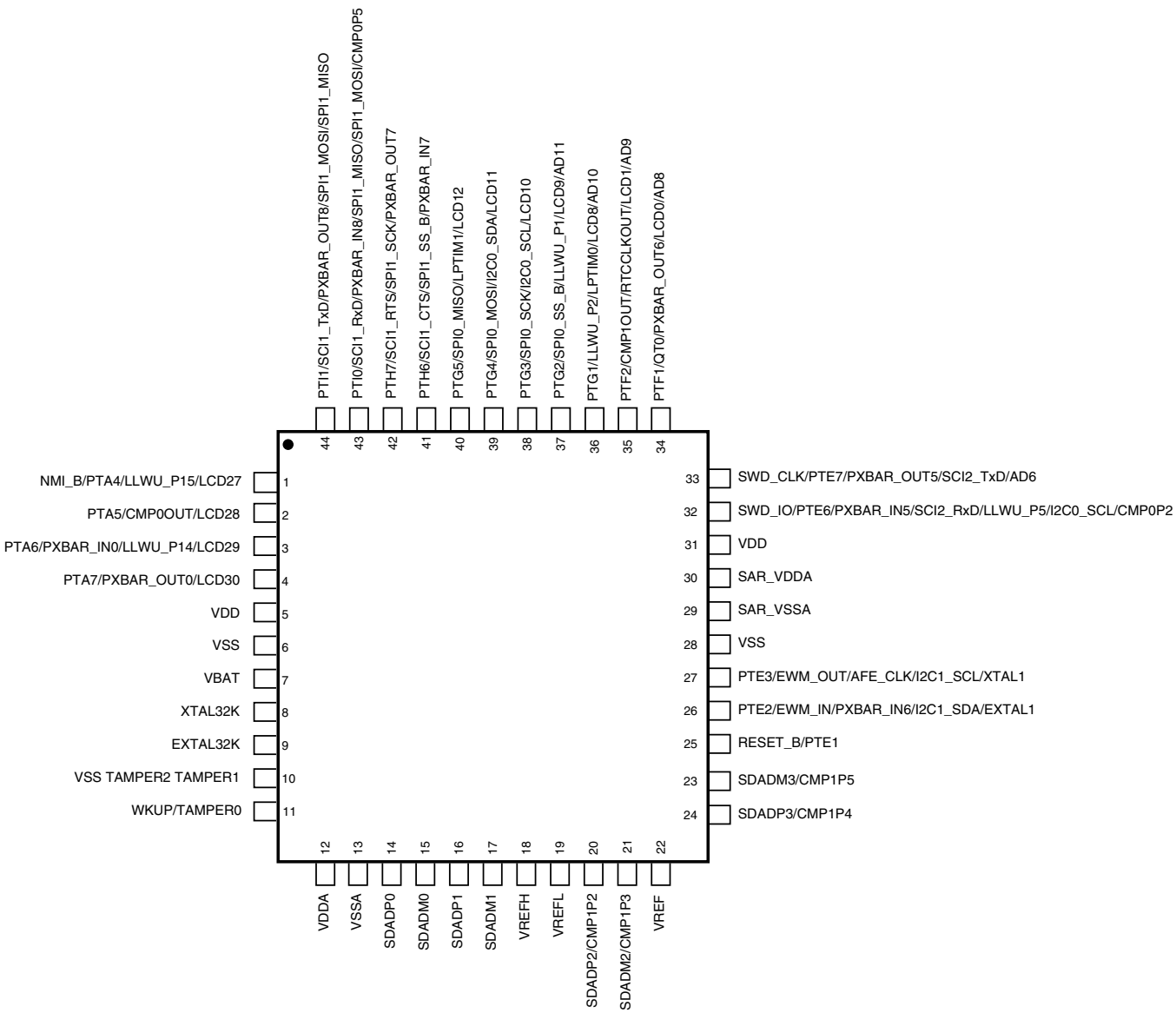


Figure 8. 44-pin LGA Pinout Diagram

NOTE

VSS also connects to flag on 44 LGA.